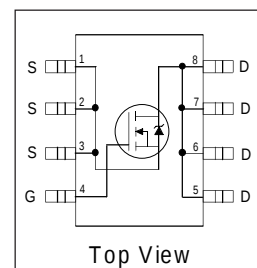
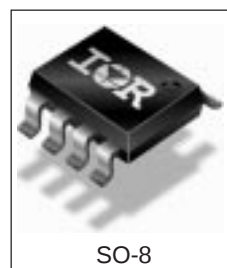


- N-Channel Application-Specific MOSFETs
- Ideal for CPU Core DC-DC Converters
- Low Conduction Losses
- Low Switching Losses
- Minimizes Parallel MOSFETs for high current applications

HEXFET® Chipset for DC-DC Converters



Description

These new devices employ advanced HEXFET® Power MOSFET technology to achieve an unprecedented balance of on-resistance and gate charge. The reduced conduction and switching losses make them ideal for high efficiency DC-DC converters that power the latest generation of microprocessors.

Both the IRF7809A and IRF7811A have been optimized and are 100% tested for all parameters that are critical in synchronous buck converters including $R_{DS(on)}$, gate charge and $C_{dv/dt}$ -induced turn-on immunity. The IRF7809A offers particularly low $R_{DS(on)}$ and high $C_{dv/dt}$ immunity for synchronous FET applications. The IRF7811A offers an extremely low combination of Q_{sw} & $R_{DS(on)}$ for reduced losses in control FET applications.

The package is designed for vapor phase, infra-red, convection, or wave soldering techniques. Power dissipation of greater than 2W is possible in a typical PCB mount application.

DEVICE RATINGS

	IRF7809A	IRF7811A
V_{DS}	30V	28V
$R_{DS(on)}$	8.5 mΩ	12 mΩ
Q_G	73 nC	23 nC
Q_{sw}	22.5 nC	7 nC
Q_{oss}	30 nC	31 nC

Absolute Maximum Ratings

Parameter		Symbol	IRF7809A	IRF7811A	Units
Drain-Source Voltage		V _{DS}	30	28	V
Gate-Source Voltage		V _{GS}	±12		
Continuous Drain or Source Current (V _{GS} ≥ 4.5V)	T _A = 25°C	I _D	14.5	11.4	A
	T _L = 90°C		14.2	11.2	
Pulsed Drain Current①		I _{DM}	100	100	
Power Dissipation	T _A = 25°C	P _D	2.5		W
	T _L = 90°C		2.4		
Junction & Storage Temperature Range		T _J , T _{STG}	−55 to 150		°C
Continuous Source Current (Body Diode)		I _S	2.5	2.5	A
Pulsed Source Current①		I _{SM}	50	50	

Thermal Resistance

Parameter		Max.	Units
Maximum Junction-to-Ambient③	$R_{\theta JA}$	50	$^\circ C/W$
Maximum Junction-to-Lead	$R_{\theta JL}$	25	$^\circ C/W$

IRF7809A/IRF7811A

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IR Rectifier

Electrical Characteristics		IRF7809A			IRF7811A			Units	Conditions
Parameter		Min	Typ	Max	Min	Typ	Max		
Drain-to-Source Breakdown Voltage*	BV_{DSS}	30	—	—	28	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
Static Drain-Source on Resistance*	$R_{DS(on)}$		7	8.5		10	12	m Ω	$V_{GS} = 4.5V, I_D = 15A$ ②
Gate Threshold Voltage*	$V_{GS(th)}$	1.0			1.0			V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Drain-Source Leakage Current*	I_{DSS}			30			30	μA	$V_{DS} = 24V, V_{GS} = 0$
				150			150		$V_{DS} = 24V, V_{GS} = 0,$ $T_J = 100^\circ C$
Gate-Source Leakage Current*	I_{GSS}			± 100			± 100	nA	$V_{GS} = \pm 12V$
Total Gate Chg Cont FET*	Q_G		61	75		19	23	nC	$V_{GS}=5V, I_D=15A, V_{DS}=16V$
Total Gate Chg Sync FET*	Q_G		55	73		17	20.5		$V_{GS} = 5V, V_{DS} < 100mV$
Pre-Vth Gate-Source Charge	Q_{GS1}		14			2.7			$V_{DS} = 16V, I_D = 15A$
Post-Vth Gate-Source Charge	Q_{GS2}		3.5			1.3			
Gate to Drain Charge	Q_{GD}		13.5			4.5			
Switch Chg($Q_{GS2} + Q_{GD}$)*	Q_{SW}		17	22.5		5.8	7.0		
Output Charge*	Q_{OSS}		25	30		26	31		$V_{DS} = 16V, V_{GS} = 0$
Gate Resistance	R_G		1.1			1.8		Ω	
Turn-on Delay Time	$t_{d(on)}$		19			8		ns	$V_{DD} = 16V, I_D = 15A$ $V_{GS} = 5V$ Clamped Inductive Load
Rise Time	t_r		9			4			
Turn-off Delay Time	$t_{d(off)}$		32			16			
Fall Time	t_f		12			8			
Input Capacitance	C_{iss}	—	7300	—	—	1800	—	pF	$V_{DS} = 16V, V_{GS} = 0$
Output Capacitance	C_{oss}	—	900	—	—	900	—		
Reverse Transfer Capacitance	C_{rss}	—	350	—	—	60	—		

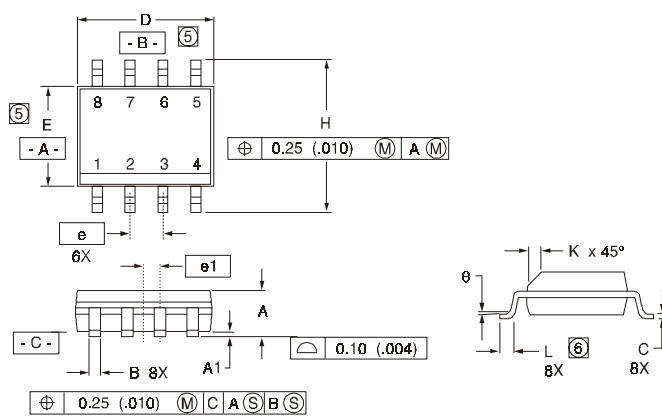
Source-Drain Rating & Characteristics

Parameter		Min	Typ	Max	Min	Typ	Max	Units	Conditions
Diode Forward Voltage*	V_{SD}			1.0			1.0	V	$I_S = 15A$ ②, $V_{GS} = 0V$
Reverse Recovery Charge④	Q_{rr}		94			82		nC	$di/dt \sim 700A/\mu s$ $V_{DS} = 16V, V_{GS} = 0V, I_S = 15A$
Reverse Recovery Charge (with Parallel Schottky)④	$Q_{rr(s)}$		87			74			$di/dt = 700A/\mu s$ (with 10BQ040) $V_{DS} = 16V, V_{GS} = 0V, I_S = 15A$

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.
- ③ When mounted on 1 inch square copper board, $t < 10$ sec.
- ④ Typ = measured - Q_{OSS}
- * Devices are 100% tested to these parameters.

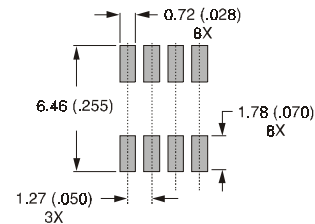
SO-8 Package Outline



NOTES:

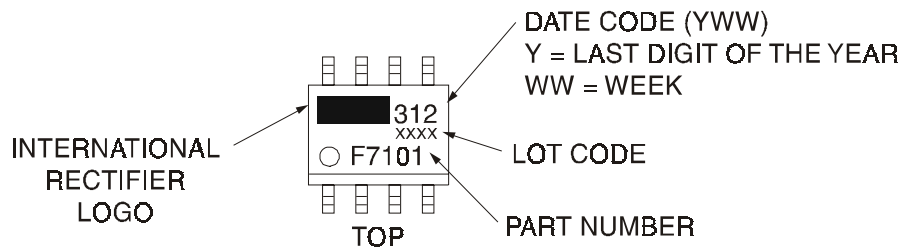
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS
MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.006).
6. DIMENSIONS IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE..

RECOMMENDED FOOTPRINT



Part Marking Information

EXAMPLE: THIS IS AN IRF7101

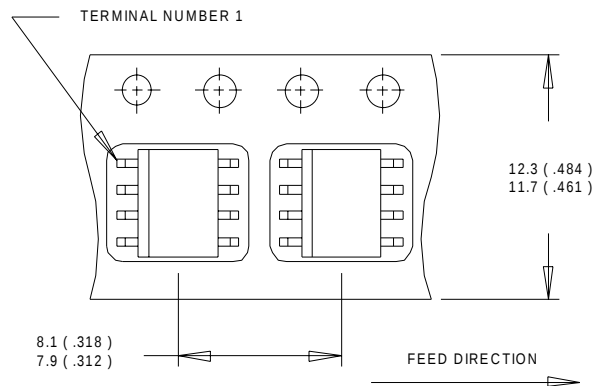


IRF7809A/IRF7811A

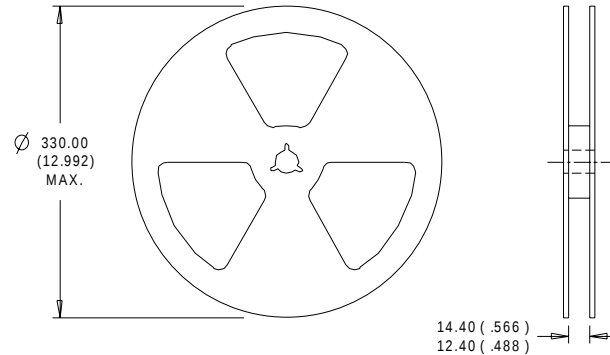
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SO-8 Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

International
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IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

IR JAPAN: K&H Bldg., 2F, 3-30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo 171-0021 Japan Tel: 81 3 3983 0086

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<http://www.irf.com/> Data and specifications subject to change without notice. 1/00